

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	158	fazli and erdem	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:10
L2	162	semiconductor same ((sensing or sensor) adj layer) same (electrode or contact)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:11
L3	27	semiconductor same ((sensing or sensor) adj layer) same (electrode or contact) same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:12
L4	227	semiconductor and ((sensing or sensor) adj layer) and (electrode or contact) and gate and (source or drain or source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:12
L5	9	semiconductor and ((sensing or sensor) adj layer) and (electrode or contact) and gate and (source or drain or source/drain) and ((expose or exposing or exposed or exposure) near5 ((sensor or sensing) adj layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:13
L6	6	semiconductor and ((sensing or sensor) adj layer) and (electrode or contact) and gate and (source or drain or source/drain) and ((expose or exposing or exposed or exposure) near5 ((sensor or sensing) adj layer)) and (fet or (field adj effect adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:14
L7	106	semiconductor and ((sensing or sensor) adj layer) and (electrode or contact) and gate and (source or drain or source/drain) and (((sensor or sensing) adj layer)) and (fet or (field adj effect adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:15
L8	53	semiconductor and ((sensing or sensor) adj layer) and (electrode or contact).clm. and gate and (source or drain or source/drain) and (((sensor or sensing) adj layer)) and (fet or (field adj effect adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:15

L9	19	semiconductor and ((sensing or sensor) adj layer) and (electrode or contact).clm. and gate.clm. and (source or drain or source/drain) and (((sensor or sensing) adj layer)) and (fet or (field adj effect adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:15
L10	9	semiconductor and ((sensing or sensor) adj layer) and (electrode or contact).clm. and gate.clm. and (source or drain or source/drain) and (((sensor or sensing) adj layer)).clm. and (fet or (field adj effect adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:15
L11	9	semiconductor and ((sensing or sensor) adj layer) and (electrode or contact).clm. and gate.clm. and (source or drain or source/drain). clm. and (((sensor or sensing) adj layer)).clm. and (fet or (field adj effect adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:15
L12	8	semiconductor and ((sensing or sensor) adj layer) and (electrode or contact).clm. and gate.clm. and (source or drain or source/drain). clm. and (((sensor or sensing) adj layer)).clm. and (fet or (field adj effect adj transistor)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:16
L13	1	semiconductor and ((sensing or sensor) adj layer) and (electrode or contact).clm. and gate.clm. and (source or drain or source/drain). clm. and (((sensor or sensing) adj layer)).clm. and (fet or (field adj effect adj transistor)).clm. and ph. clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:16
L14	1	semiconductor and ((sensing or sensor) adj layer) and (electrode or contact).clm. and gate.clm. and (source or drain or source/drain). clm. and (fet or (field adj effect adj transistor)).clm. and ph.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:17
L15	6528	(sensor or detector or detecting or detection or sensing).clm. and (fet or (field adj effect adj transistor)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:17
L16	3983	(sensor or detector or detecting or detection or sensing).clm. and (fet or (field adj effect adj transistor)). clm. and gate.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:17

L17	1541	(sensor or detector or detecting or detection or sensing) same (fet or (field adj effect adj transistor)). clm. and gate.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:17
L18	1151	(sensor or detector or detecting or detection or sensing) same (fet or (field adj effect adj transistor)) same gate.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:18
L19	5871	(sensor or detector or detecting or detection or sensing) same (fet or (field adj effect adj transistor)) same gate same (source or drain or source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:18
L20	151	(sensor or detector or detecting or detection or sensing) same (fet or (field adj effect adj transistor)) same gate same (source or drain or source/drain) same (expose or exposing or exposed or exposure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:18
L21	23	(sensor or detector or detecting or detection or sensing) same (fet or (field adj effect adj transistor)) same gate same (source or drain or source/drain) same (expose or exposing or exposed or exposure) and ph	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 22:18